Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"20040238124"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 10:13
L2	1884	(plural$4 near2 plasma)	US-PGPUB; USPAT	OR	ON	2005/11/05 11:20
L3	350065	"118"/$.ccls. "156"/$.ccls. "427"/$.ccls. "204"/$.ccls. "438"/$.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/05 11:21
L4	866	L3 AND 2	US-PGPUB; USPAT	OR	ON	2005/11/05 11:21
L5	103	4 AND (PLURAL$4 NEAR ELECTROD$3)	US-PGPUB; USPAT	OR	ON	2005/11/05 14:04
L6	1	"20030106788"	US-PGPUB; USPAT	OR	ON	2005/11/05 12:40
L7	1	"5652029".pn.	US-PGPUB; USPAT	OR	ON	2005/11/05 12:40
L8	1	"6001432".pn.	US-PGPUB; USPAT	OR	ON	2005/11/05 12:41
L9	801	4 AND (voltage control$4)	US-PGPUB; USPAT	OR	ON	2005/11/05 12:46
L10	259	4 AND (voltage same control$4)	US-PGPUB; USPAT	OR	ON	2005/11/05 12:46
L11	136	4 AND (voltage near3 control$4)	US-PGPUB; USPAT	OR	ON	2005/11/05 14:01
L12	1	"5652029".pn.	US-PGPUB; USPAT	OR	ON	2005/11/05 14:01
L13	0	5 and (atmospher and lithograph)	US-PGPUB; USPAT	OR	ON	2005/11/05 14:05
L14	0	5 and (atmospher and beam)	US-PGPUB; USPAT	OR	ON	2005/11/05 14:03
L15	0	4 AND (atmospher and lithograph)	US-PGPUB; USPAT	OR	ON	2005/11/05 14:04
L16	0	4 AND (atmospher and beam)	US-PGPUB; USPAT	OR	ON	2005/11/05 14:04
L17	0	5 and lithograph	US-PGPUB; USPAT	OR	ON	2005/11/05 14:05
L18	40	5 and beam	US-PGPUB; USPAT	OR	ON	2005/11/05 14:14
L19	22386	(plural$4 near3 electrode)	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:15
L20	497	19 and (electrode near4 (lithograph beam))	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:18

L21	0	20 and atmospher	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:16
L22	1	20 and (plural$4 near2 plasma)	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:17
L23	365	19 and (electrode near3 (lithograph beam))	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:18
L24	173	19 and (electrode near2 (lithograph beam))	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:30
L25	197	19 and ((electrode made mak$3) near2 (lithograph beam))	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:31
L26	1	19 and ((electrode near2 made) near2 (lithograph beam))	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:31
L27	43	19 and ((electrode near2 made) same (lithograph beam))	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:54
L28	1	"20040115402"	EPO; JPO; DERWENT	OR	ON	2005/11/05 14:55
L29	2	"20040115402"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/05 14:56
L30	2	"6236163".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/05 15:00
L37	2	"6538387".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 15:43
L38	2	"4620893".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 15:43
L39	182	(osamu near2 nakamura).in.	US-PGPUB; USPAT	OR	ON	2005/11/05 16:13
L40	24	L39 and (plural$4 near3 electrode)	US-PGPUB; USPAT	OR	ON	2005/11/05 16:17
L41	24	L39 and (plural$4 near4 electrode)	US-PGPUB; USPAT	OR	ON	2005/11/05 16:17
L42	0	13 and (plural$4 near4 electrode)	US-PGPUB; USPAT	OR	ON	2005/11/05 16:18
L43	3925	(semiconductor near energy near laboratory).as.	US-PGPUB; USPAT	OR	ON	2005/11/05 16:18
L44	817	L43 and (plural$4 near4 electrode)	US-PGPUB; USPAT	OR	ON	2005/11/05 16:18

L45	21	44 and (plural$4 near3 plasma)	US-PGPUB; USPAT	OR	ON	2005/11/05 16:24
L46	28	44 and (plural$4 near4 plasma)	US-PGPUB; USPAT	OR	ON	2005/11/05 16:25
L47	7	46 not 45	US-PGPUB; USPAT	OR	ON	2005/11/05 16:25
S1	2	"20050039679"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/05 10:13
S2	2	"20040028837"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 09:35
S3	2	"5717294".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 09:35
S4	2	"20040238124"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/04 11:58
S5	7	"5652029".pn. "6001431".pn. "6001432".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/04 14:16
S6	86	156/345.38.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/04 14:22
S7	73	156/345.45.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/04 14:43
S8	1601	118/719.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/04 15:13
S9	328	156/345.47.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/04 15:34
S10	1403	118/723E.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/04 17:13
S11	182	(osamu near2 nakamura).in.	US-PGPUB; USPAT	OR	ON	2005/11/05 16:12
S12	103	S11 and electrode	US-PGPUB; USPAT	OR	ON	2005/11/04 17:21

S13	3925	(semiconductor near energy near laboratory).as.	US-PGPUB; USPAT	OR	ON	2005/11/05 16:17
S14	817	S13 and (electrode near4 plural$4)	US-PGPUB; USPAT	OR	ON	2005/11/04 17:22
S15	657	S13 and (electrode near2 plural$4)	US-PGPUB; USPAT	OR	ON	2005/11/04 17:23
S16	15	S15 and (plural$4 near3 plasma)	US-PGPUB; USPAT	OR	ON	2005/11/04 17:26
S17	350065	"118"/$.ccls. "156"/$.ccls. "427"/$.ccls. "204"/$.ccls. "438"/$.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/05 11:21
S18	1884	((plural$4 near2 plasma) same (plural$4 electrode))	US-PGPUB; USPAT	OR	ON	2005/11/05 11:20
S19	866	S17 and S18	US-PGPUB; USPAT	OR	ON	2005/11/04 18:03
S20	254	((plural$4 near2 plasma near2 generat$4) same (plural$4 electrode))	US-PGPUB; USPAT	OR	ON	2005/11/04 18:22
S21	153	S17 and S20	US-PGPUB; USPAT	OR	ON	2005/11/04 17:30
S22	113	S19 and (atmospher$3 near3 plasma)	US-PGPUB; USPAT	OR	ON	2005/11/04 18:21
S23	0	S19 and (atmospher$3 near3 plasma)	EPO; JPO; DERWENT	OR	ON	2005/11/04 18:21
S24	3506	(atmospher$3 near3 plasma)	EPO; JPO; DERWENT	OR	ON	2005/11/04 18:23
S25	0	S24 and ((plural$4 near2 plasma near2 generat$4) same (plural$4 electrode))	US-PGPUB; USPAT	OR	ON	2005/11/04 18:22
S26	0	S24 and (plural$4 electrode)	US-PGPUB; USPAT	OR	ON	2005/11/04 18:22
S27	5	S24 and ((plural$4 near2 plasma near2 generat$4) same (plural$4 electrode))	EPO; JPO; DERWENT	OR	ON	2005/11/04 18:25
S28	5	S24 and ((plural$4 near2 plasma near2 generat$4))	EPO; JPO; DERWENT	OR	ON	2005/11/04 18:25
S29	23	S24 and ((plural$4 near2 electrode))	EPO; JPO; DERWENT	OR	ON	2005/11/04 18:43
S30	1	"20040261717"	EPO; JPO; DERWENT	OR	ON	2005/11/04 18:43
S31	1	"20040261717"	US-PGPUB; USPAT	OR	ON	2005/11/04 18:43